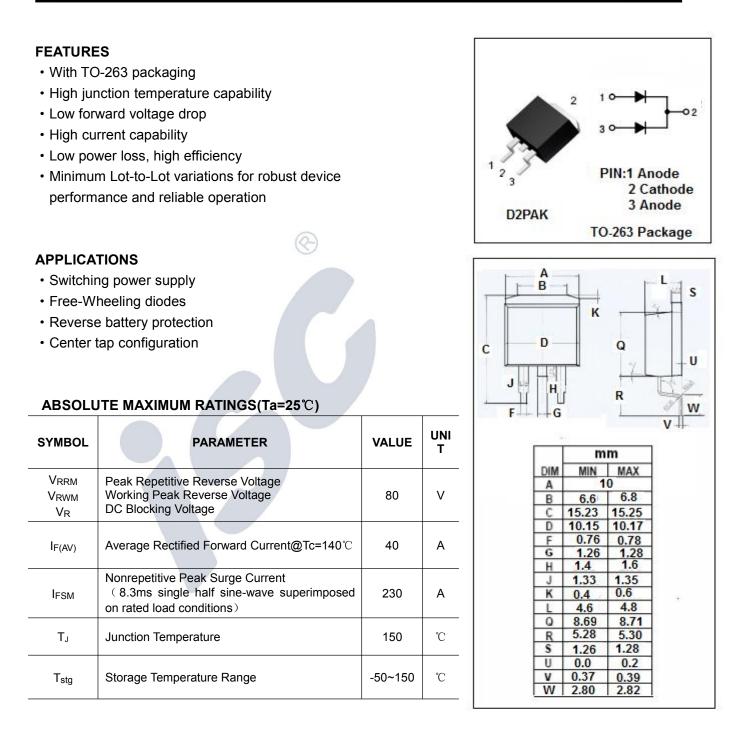


Schottky Barrier Rectifier

INCHANGE SEMICONDUCTOR

SBRT40M80CTB





Schottky Barrier Rectifier

SBRT40M80CTB

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	МАХ	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	1.5	°C/W

ELECTRICAL CHARACTERISTICS (Pulse Test: Pulse Width=300 µ s,Duty Cycle≤1%)

SYMBOL	PARAMETER	CONDITIONS	МАХ	UNIT
VF	Maximum Instantaneous Forward Voltage	I _F = 10A ; Tc= 25 ℃	0.59	V
		I _F = 20A ; Tc= 25 ℃	0.72	
		I _F = 20A ; Tc= 125℃	0.63	
IR	Maximum Instantaneous Reverse Current	V _R = V _{RWM:} Tc= 25℃	0.065	mA
		V _R =0.8*V _{RWM;} Tc= 125°С	40	



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